PNP Silicon Epitaxial Transistors

This PNP Silicon Epitaxial transistor is designed for use in audio amplifier applications. The device is housed in the SOT–223 package which is designed for medium power surface mount applications.

- High Current
- NPN Complement is BCP56
- The SOT-223 Package can be soldered using wave or reflow.
 The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Device Marking:

BCP53T1 = AH

BCP53-10T1 = AH-10

BCP53-16T1 = AH-16

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector–Emitter Voltage	V _{CEO}	-80	Vdc	
Collector-Base Voltage	V _{CBO}	-100	Vdc	
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc	
Collector Current	Ic	1.5	Adc	
Total Power Dissipation @ T _A = 25°C (Note 1) Derate above 25°C	P _D	1.5 12	W mW/°C	
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.

THERMAL CHARACTERISTICS

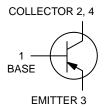
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Surface Mounted)	$R_{\theta JA}$	83.3	°C/W
Lead Temperature for Soldering, 0.0625" from case Time in Solder Bath	T _L	260 10	°C s



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MEDIUM POWER HIGH CURRENT SURFACE MOUNT PNP TRANSISTORS



MARKING DIAGRAM



STYLE 1



A = Assembly Location

Y = Year

W = Work Week

XXXXX = Specific Device Code • Pb-Free Package

(*Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BCP53T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					1
Collector–Base Breakdown Voltage (I _C = –100 μAdc, I _E = 0)	V _(BR) CBO	-100	-	-	Vdc
Collector–Emitter Breakdown Voltage (I _C = -1.0 mAdc, I _B = 0)	V _{(BR)CEO}	-80	-	-	Vdc
Collector–Emitter Breakdown Voltage ($I_C = -100 \mu Adc, R_{BE} = 1.0 k\Omega$)	V _(BR) CER	-100	-	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	-5.0	-	-	Vdc
Collector–Base Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	I _{CBO}	-	_	-100	nAdc
Emitter–Base Cutoff Current (V _{EB} = -5.0 Vdc, I _C = 0)	I _{EBO}	_	-	-10	μAdc
ON CHARACTERISTICS	·				
DC Current Gain $ \begin{aligned} &(I_C=-5.0 \text{ mAdc, V}_{CE}=-2.0 \text{ Vdc}) \\ &\text{All Part Types} \\ &(I_C=-150 \text{ mAdc, V}_{CE}=-2.0 \text{ Vdc}) \\ &\text{BCP53, SBCP53} \\ &\text{BCP53}-10, \text{SBCP53}-10 \\ &\text{BCP53}-16, \text{SBCP53}-16 \\ &(I_C=-500 \text{ mAdc, V}_{CE}=-2.0 \text{ Vdc}) \\ &\text{All Part Types} \end{aligned} $	h _{FE}	25 40 63 100 25	- - - -	- 250 160 250	_
Collector–Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)	V _{CE(sat)}	_	-	-0.5	Vdc
Base–Emitter On Voltage (I _C = -500 mAdc, V _{CE} = -2.0 Vdc)	V _{BE(on)}	_	-	-1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain – Bandwidth Product (I _C = –10 mAdc, V _{CE} = –5.0 Vdc, f = 35 MHz)	f _T	_	50	_	MHz

TYPICAL CHARACTERISTICS

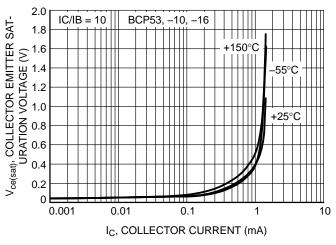


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

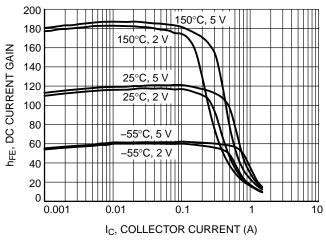


Figure 2. DC Current Gain vs. Collector Current (BCP53)

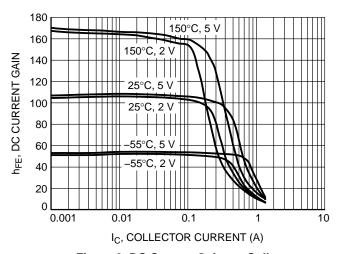


Figure 3. DC Current Gain vs. Collector Current (BCP53-10)

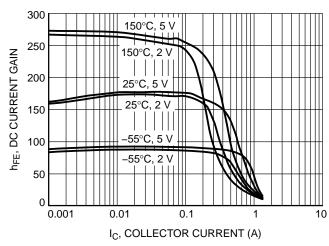


Figure 4. DC Current Gain vs. Collector Current (BCP53-16)

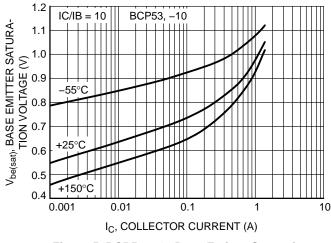


Figure 5. BCP53, -10 Base Emitter Saturation Voltage vs. Collector Current

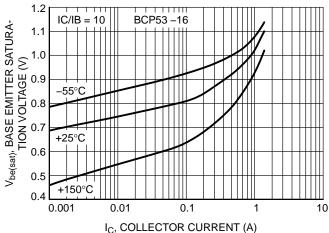


Figure 6. BCP53–16 Base Emitter Saturation Voltage vs. Collector Current

TYPICAL CHARACTERISTICS

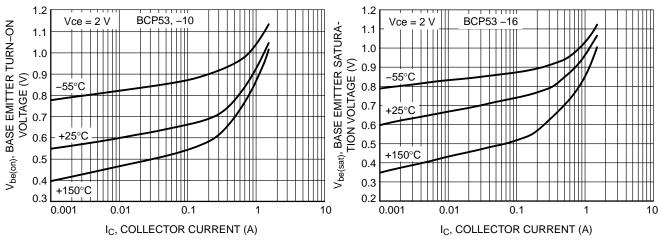


Figure 7. BCP53, -10 Base Emitter Turn-On Voltage vs. Collector Current V_{BE(on)}

Figure 8. BCP53–16 Base Emitter Turn-On Voltage vs. Collector Current

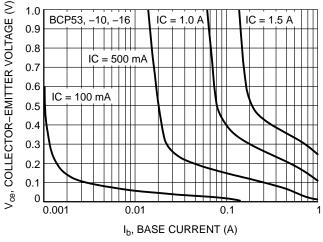


Figure 9. BCP53, -10, -16 Saturation Region

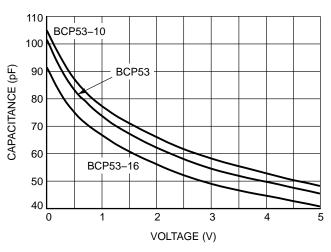


Figure 10. Input Capacitance

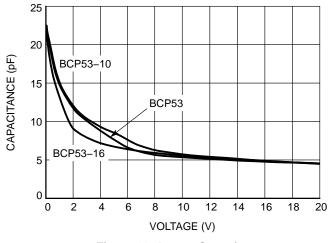


Figure 11. Output Capacitance

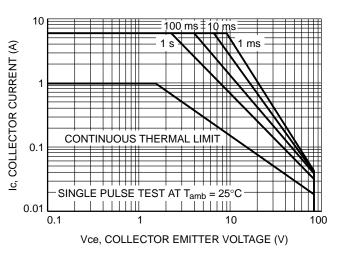
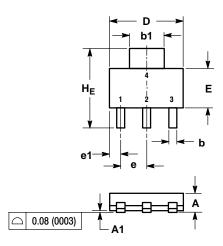
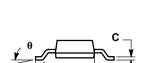


Figure 12. Standard Operating Area

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE N





NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M,

1994.

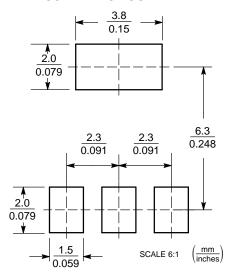
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
С	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20			0.008		
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	_	10°	0°	_	10°

STYLE 1:

- PIN 1. BASE 2. COLLECTOR
 - 3. EMITTER
 4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb—Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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